

(51) International Patent Classification:
C09K 3/14 (2006.01) *H01L 21/304* (2006.01)(21) International Application Number:
PCT/US2010/039118(22) International Filing Date:
18 June 2010 (18.06.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
61/219,031 22 June 2009 (22.06.2009) US(71) Applicant (for all designated States except US): **CABOT MICROELECTRONICS CORPORATION** [US/US]; Legal Department, 870 N. Commons Drive, Aurora, Illinois 60504 (US).

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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- as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))
- as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))

[Continued on next page]

(54) Title: CMP COMPOSITIONS AND METHODS FOR SUPPRESSING POLYSILICON REMOVAL RATES

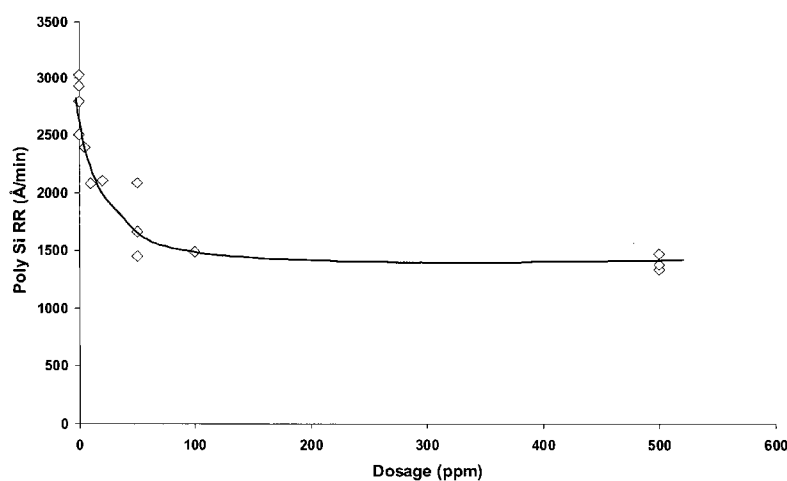


FIG. 2

(57) Abstract: The present invention provides a chemical-mechanical polishing (CMP) composition suitable for polishing a silicon nitride-containing substrate while suppressing polysilicon removal from the substrate. The composition comprises abrasive particles suspended in an acidic aqueous carrier containing a surfactant comprising an alkyne-diol, an alkyne diol ethoxylate, or a combination thereof. Methods of polishing a semiconductor substrate therewith are also disclosed.



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